

**IN THE CLAIMS**

1.-9. (canceled)

10. (currently amended): [[A]] The semiconductor apparatus according to claim 14,  
further comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material;

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer; and

an electrically conductive layer disposed between said adhesion layer and said semiconductor thin film.

11.-12. (canceled)

13. (currently amended): ~~The semiconductor apparatus according to claim 12, further comprising~~

A semiconductor apparatus comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material;

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer;

an individual interconnecting layer extending from an upper surface of said semiconductor thin film to an upper surface of a terminal area of said integrated circuit so that said semiconductor device and said integrated circuit are electrically connected to each other; and

a second interdielectric layer which electrically isolates said individual interconnecting layer from said semiconductor thin film and ~~apart~~ a part of said substrate.

14. (original): The semiconductor apparatus according to claim 13, wherein said second interdielectric layer including at least one of a silicon oxide film and a silicon nitride film.

15. (currently amended): The semiconductor apparatus according to claim ~~[[3]]~~ 13, further comprising:

an individual interconnecting layer extending from an upper surface of said semiconductor thin film to an upper surface of said substrate: and

an electrode pad disposed on said first interdielectric layer, said electrode pad being electrically connected to said individual interconnecting layer.

16.-17. (canceled)

18. (currently amended): ~~[[A]]~~ The semiconductor apparatus according to claim 33, comprising:

~~— a substrate;~~

~~— an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material; and~~

~~— at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer;~~

wherein a number of said at least one semiconductor device is plural, and a plurality of said semiconductor devices are arranged in said semiconductor thin film at regular intervals.

19. (previously presented): A semiconductor apparatus comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material; and

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer;

wherein a number of said at least one semiconductor device formed in said semiconductor thin film is one, a number of said at least one semiconductor film is plural, and a plurality of said semiconductor thin films are arranged on said adhesion layer at regular intervals.

20.-26. (canceled)

27. (currently amended): The semiconductor apparatus according to claim ~~[[26]]~~ 33, wherein said substrate is a semiconductor substrate including an integrated circuit which includes a plurality of circuit elements.

28. (previously presented): The semiconductor apparatus according to claim 27, wherein said semiconductor thin film is disposed on a region of said substrate adjacent to a region in which said integrated circuit is formed.

29. (previously presented): The semiconductor apparatus according to claim 27, wherein said semiconductor thin film is disposed on a region of said substrate in which said integrated circuit is formed.

30. (currently amended): The semiconductor apparatus according to claim ~~[[26]]~~ 33, wherein said substrate is an insulating substrate.

31. (currently amended): The semiconductor apparatus according to claim [[26]] 33, wherein said adhesion layer is any of a polycrystalline silicon layer and an amorphous silicon layer;

wherein said semiconductor thin film is a compound semiconductor thin film;

wherein ~~amain~~ a main constituent of said substrate is different from a main constituent of said semiconductor thin film.

32. (currently amended): The semiconductor apparatus according to claim [[26]] 33, wherein said semiconductor thin film is a compound semiconductor thin film.

33. (currently amended): ~~The semiconductor apparatus according to claim 26;~~

A semiconductor apparatus comprising:

a substrate;

at least one semiconductor thin film including at least one semiconductor device; and

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material, a main constituent of said adhesion layer being different from a main constituent of said at least one semiconductor thin film, said semiconductor material having an affinity to both of said at least one semiconductor thin film and said substrate;

said at least one semiconductor thin film being bonded on said adhesion layer;

wherein said semiconductor device is any of a light-emitting element, a light-sensing element, a Hall element, and a piezoelectric element.

34. (currently amended): An optical print head including the semiconductor apparatus of claim [[26]] 33.

35. (currently amended): An optical print head including the semiconductor apparatus of claim ~~[[26]]~~ 33, wherein the semiconductor device in the thin semiconductor film in the semiconductor apparatus is a light-emitting element, the semiconductor apparatus including a plurality of such light-emitting elements, the optical print head further including:

- a base for supporting the semiconductor apparatus;
- a rod lens array for focusing the light emitted by the light-emitting elements in the semiconductor apparatus;
- a holder for holding the rod lens array; and
- at least one clamp for holding the base and the holder together.

36. (currently amended): An image-forming apparatus comprising at least one optical print head including the semiconductor apparatus of claim ~~[[26]]~~ 33.

37. (previously presented): The image-forming apparatus of claim 36, further comprising:  
a photosensitive drum selectively illuminated by the optical printing head to form a latent electrostatic image.

38. (previously presented): The image-forming apparatus of claim 37, further comprising:  
a developing unit for supplying toner to develop the latent electrostatic image on the photosensitive drum; and  
a transfer roller for transferring the developed image from the photosensitive drum to printing media.